/ Revised record

D	2018-7				
E	2018-10-16				
F	2019-3-13	2			
G	2020-1-8	2 3 6	$V_{GS(th)}$! " #$%&'$( ) * + #$, - & '$( ) .V_{GSS} ! " ±20 改为±12V；I_{GSS}的条件 ! " V_{GS}=±20V 改为 V_{GS}=±12V；		

SOP-8 MOS

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

N-channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=6.9A	I_D=-6A
$R_{DS(ON)}$<32mΩ (V_{GS}=10V)	$R_{DS(ON)}$<65mΩ (V_{GS}=-10V)
$R_{DS(ON)}$<36mΩ (V_{GS}=4.5V)	$R_{DS(ON)}$<75mΩ (V_{GS}=-4.5V)

Halogen-free Product.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.

参数 Parameter	符号 Symbol	数值 Rating		单位 Unit
		N-channel	P-channel	
Drain-Source Voltage	V_{DSS}			

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	30		

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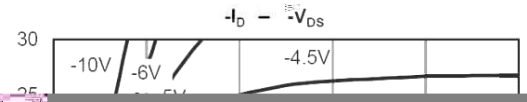
.!

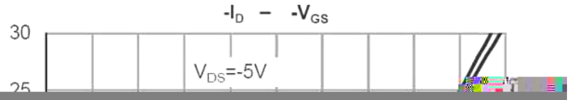
=0V

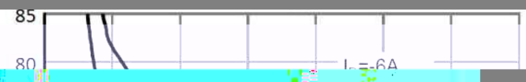
6 N− **/ N-**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}				

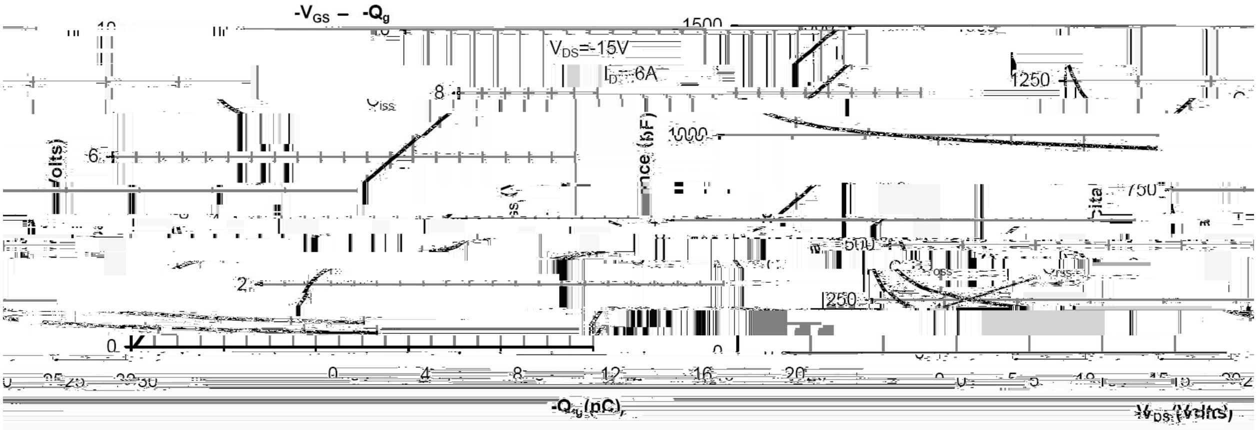
P− / P-CHANNEL Electrical Characteristic Curve

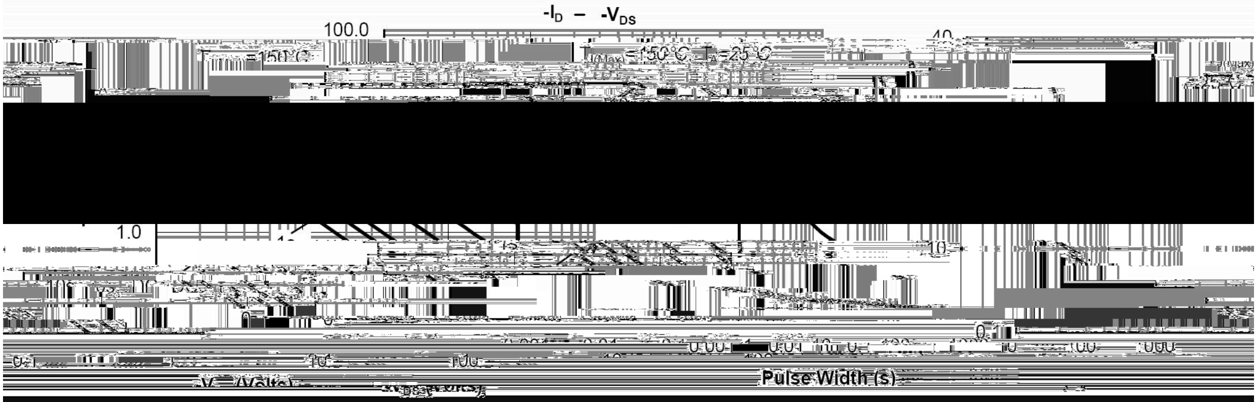


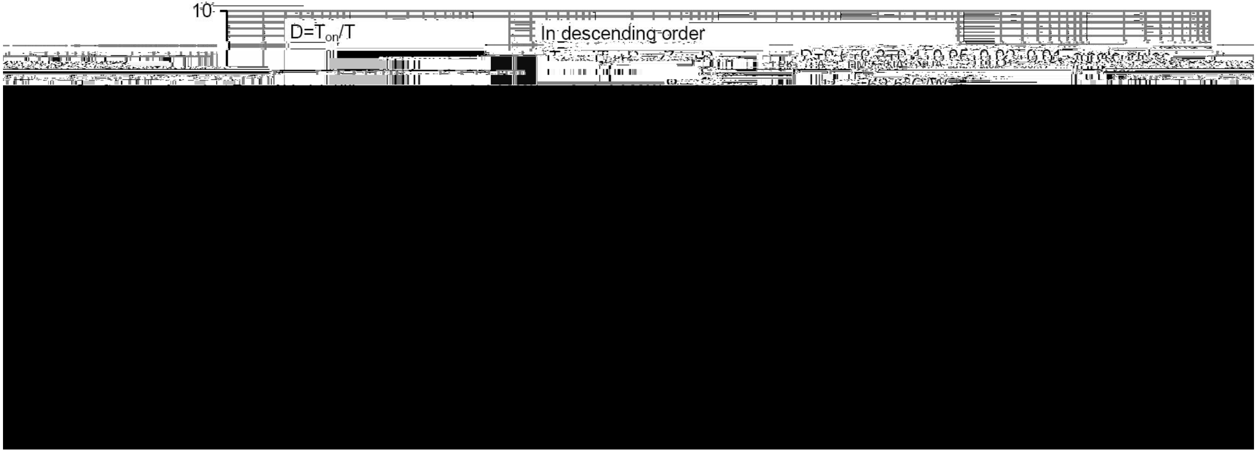




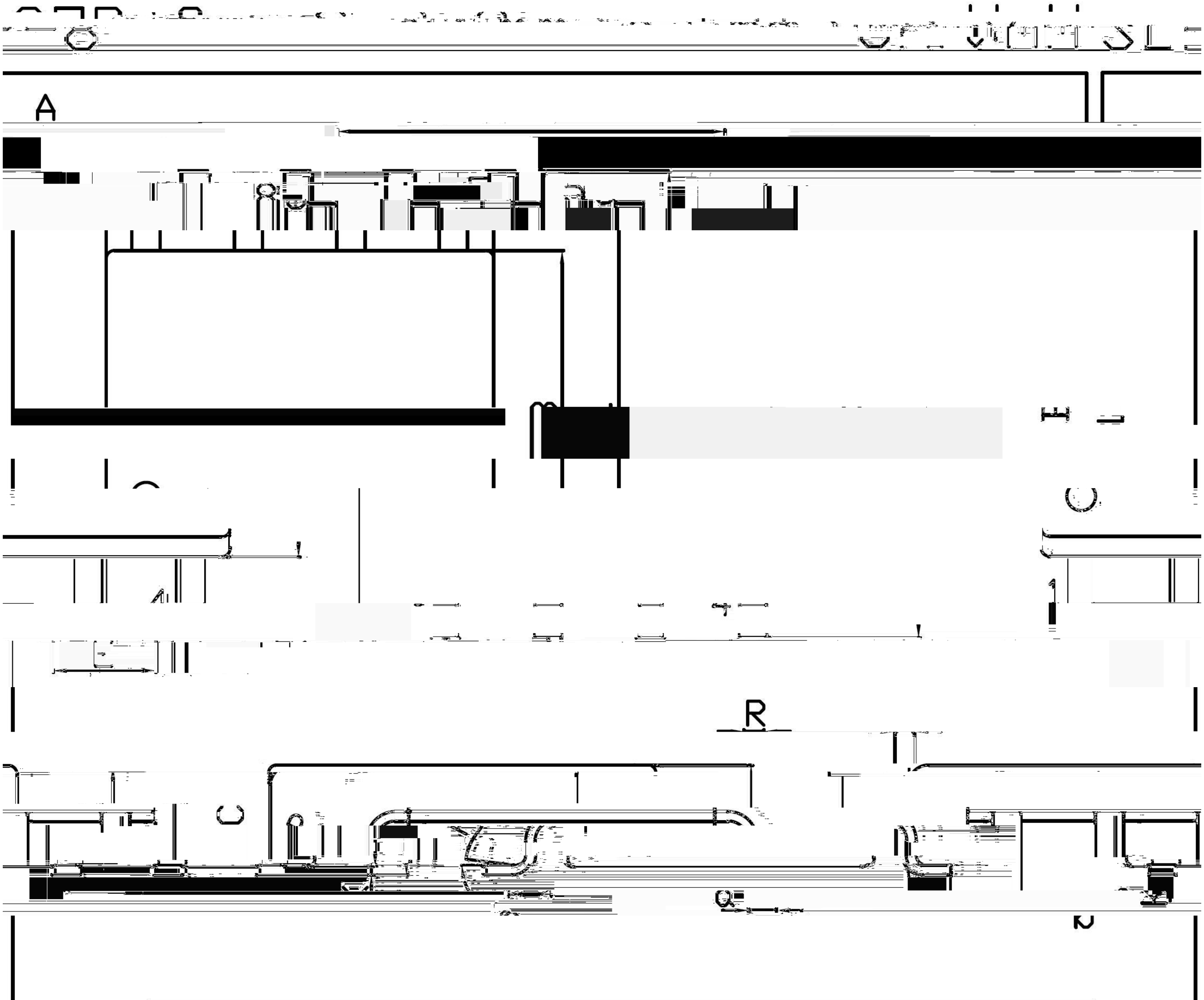
P– / P-CHANNEL Electrical Characteristic Curve





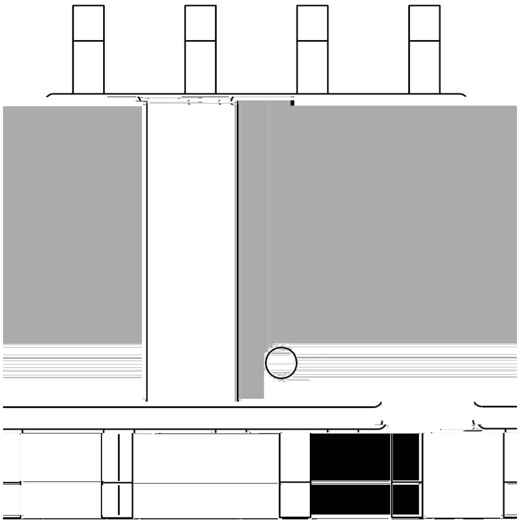


/ Package Dimensions

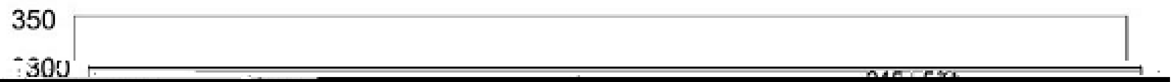


Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.70	5.10	[illegible]	1.35	1.75
B	3.70	4.10	[illegible]	0.35	0.49

/ Marking Instructions



(   ) /   Temperature Profile for IR Reflow Soldering(Pb-Free)



[redacted]

1 150 180 60 90sec;
2 245±5

Note:
1.Preheating:150~180 , Time:60~90sec.